

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0 Diameter	150.00 +/- 0.30 mm	WaferVendor
	2.0 Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0 Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	4.0 Secondary Flat Orientation	None	
	5.0 Overall Thickness	400.00 +/- 25.00 um	ADE 100% SEMI MF533
	6.0 Total Thickness Variation (TTV)	<10.00um	Guaranteed by process
	7.0 Bow	<40.00um	ADE to ASTM F534, 20%
	8.0 Warp	<40.00um	ADE to ASTM F657, 20%
	9.0 Back Surface Quality	Etched or polished	Guaranteed by process
	10.0 Front Surface Quality	Polished	Guaranteed by process
	11.0 Lasermarking	Frontside, IceMOS Standard Format: YYMM-XXXXX	
	12.0 Edge Chips	None	Bright Light 100%
	13.0 Edge Exclusion	5mm	
HandleSilicon	14.0 Handle Thickness	400.00 +/- 25.00 um	ADE 100% SEMI MF533
	15.0 Handle Growth Method	CZ	Wafer Vendor
	16.0 Handle Doping Type	N	Wafer Vendor
	17.0 Handle Dopant	Phosphorus	Wafer Vendor
	18.0 Handle Resistivity	1- 5 ohm-cm	Wafer Vendor
	19.0 Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	20.0 Surface Haze	None	Bright Light, 100% (note 2).
	21.0 Total scratch length	< 25mm Total Length	Bright Light, 100% (note 2).

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information